SILICON SMALL-SIGNAL TRANSISTOR DICE (continued)

DIE NO. 2C3439 — NPN
LINE SOURCE — DSL242

This die provides performance similar to that of the following device types:

2N3439
2N3440
MM420
MM421

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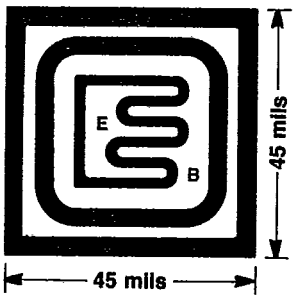
Designed for high-voltage audio and video amplifier applications.



Backside Collector

METALLIZATION —
Top ..... Al
Back ..... Au

BACKSIDE GOLD 3000Å

DIE THICKNESS ..... 6 ± 2 mils

BONDING PAD SIZE —
Emitter ..... 4.0 x 7.0 mils
Base ..... 4.0 x 7.0 mils

GLASSIVATION — The die active area, except for bond windows, is covered with Glassivation to protect from contaminants and accidental bonding.

ELECTRICAL CHARACTERISTICS (T_A = 25°C; Note 1)

Parameter	Test Conditions	Min	Max	Unit
BV_{CEO}	I_C = 50 mAdc, I_B = 0	350	—	Vdc
BV_{CBO}	I_C = 20 μAdc, I_E = 0	360	—	Vdc
BV_{EBO}	I_E = 20 μAdc, I_C = 0	6.0	—	Vdc
h_{FE}	I_C = 20 mAdc, V_{CE} = 10 Vdc	40	160	—

NOTES: 1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width ≤ 300 μs, duty cycle ≤ 2%.
2. Detailed device characteristics are available from your Motorola sales representative.